

Amendments to the Claims:

This listing of claims will replace the listing of claims as pending in the present application:

Listing of Claims:

Claim 1 (original): A nickel alloy sputtering target comprising 1 to 30at% of Cu; 2 to 25at% of at least one element selected from among V, Cr, Al, Si, Ti and Mo; remnant Ni and unavoidable impurities so as to inhibit the Sn diffusion between a solder bump and a substrate layer or a pad.

Claim 2 (original): The nickel alloy sputtering target according to claim 1, wherein the nickel alloy is formed by adding at least one element selected from among V, Cr, Al, Si, Ti and Mo to Ni-Cu solid solution.

Claim 3 (canceled).

Claim 4 (original): A nickel alloy thin film formed between a solder bump and a substrate layer or a pad, and comprising 1 to 30at% of Cu; 2 to 25at% of at least one element selected from among V, Cr, Al, Si, Ti and Mo; remnant Ni and unavoidable impurities.

Claim 5 (original): The nickel alloy thin film formed between a solder bump and a substrate layer or a pad according to claim 4, wherein the nickel alloy is formed by adding at least one element selected from among V, Cr, Al, Si, Ti and Mo to Ni-Cu solid solution.

Claims 6-8 (canceled).